TIGER ELECTRONIC CO.,LTD

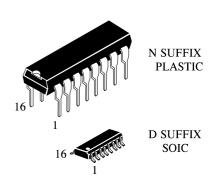
WNP 4225 CP 1 CF T

'UGXGP 'DARLINGTON'ARRAYS

The WNP 4225A are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven n-p-n Darlington pairs that feature high-voltage outputs with commoncathode clamp diodes for switching inductive loads. The collectorcurrent rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

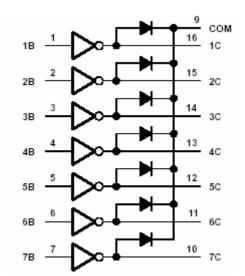
The WNP 2003A has a 2.7-k series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

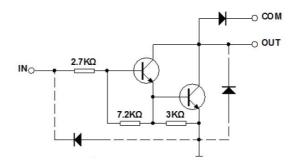
- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications



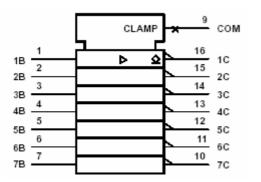
ORDERING INFORMATION WNN2003AN """ Plastic WLN2003ADT SOIC $T_A = -20^{\circ}C$ to 85° C for all packages

LOGIC DIAGRAM





LOGIC SYSBOL



SCHEMATICS (each Darlington Pair)

All resistor values shown are nominal.

WLN2003A: $R_B = 2.7 \text{ kW}$

Absolute maximum ratings at 25°C free-air temperature (unles	ss otherwise noted)
Collector-emitter voltage	50 V
Input voltage, V_I (see Note 1)	30 V Peak
collector current (see Figures 14 and 15)	500 mA
Output clamp current, I _{OK}	500 mA
Total emitter-terminal current	-2.5 A
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A	-20° C to 85° C
Storage temperature range, Tstg	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

DISSIPATION RATING TABLE				
PACKAGE	T _A = 25℃ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 85℃ POWER RATING	
D	950 mW	7.6 mW/ºC	494 mW	
N	1150 mW	9.2 mW/ºC	598 mW	

Electrical characteristics, TA = 25°C (unless otherwise noted)

PARAMETER		TEST	TEST CONDITIONS		ULN2003A			DISC.	
		FIGURE			MIN	TYP	MAX	UNIT	
	On-state input voltage	6	1	I _C = 125 mA					
				$I_C = 200 \text{ mA}$			2.4	v	
VI(on)			V _{CE} = 2 V	$I_C = 250 \text{ mA}$			2.7		
				$I_C = 275 \text{ mA}$					
				IC = 300 mA			3		
				IC = 350 mA					
	Collector-emitter	II = 250 μA,	Ic = 100 mA		0.9	1.1			
VCE(sat)		5	II = 350 μA,	Ic = 200 mA		1	1.3	V	
or or sau	saturation voltage		IJ = 500 μA,	Ic = 350 mA		1.2	1.6		
	Collector cutoff current	1	VCE = 50 V,	lj = 0			50		
ICEX		or cutoff current 2	VCE = 50 V,	II = 0			100	μA	
				VI = 1 V					
VF	Clamp forward voltage	8	IF = 350 mA			1.7	2	V	
ll(off)	Off-state input current	3	VCE = 50 V, T _A = 70°C	I _C = 500 μA,	50	65		μA	
	Input current		VI = 3.85 V			0.93	1.35		
ų		4	$V_I = 5 V$		1			mA	
3			VI = 12 V						
	0	-	V _R = 50 V				50		
IR Clamp reverse current	Clamp reverse current 7	V _R = 50 V,	T _A = 70°C			100	μA		
Ci	Input capacitance		$V_{I} = 0,$	f = 1 MHz		15	25	pF	

switching characteristics, T_A = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
^t PLH	Propagation delay time, low-to-high-level output	See Figure 9		0.25	1	μS
^t PHL	Propagation delay time, high-to-low-level output	dee rigule a		0.25	1	μS
Vон	High-level output voltage after switching	V_S = 50 V, $I_O \approx$ 300 mA, See Figure 10	VS-20			mV

PARAMETER MEASUREMENT INFORMATION

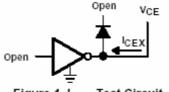


Figure 1. ICEX Test Circuit

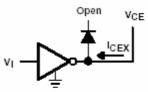


Figure 2. ICEX Test Circuit

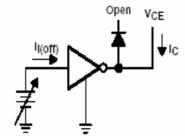


Figure 3. I_{I(off)} Test Circuit

Open

VCE

NOTE: It is fixed for measuring VCE(sat), variable for

Figure 5. hFE, VCE(sat) Test Circuit

measuring h_{FE}.

4

hFE = IC

Ic

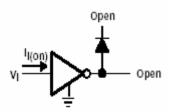


Figure 4. I_I Test Circuit

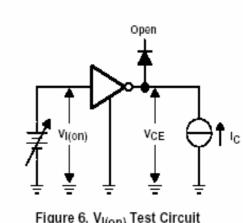
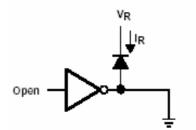


Figure 6. VI(on) Test Circuit



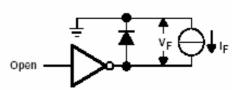


Figure 7. I_R Test Circuit



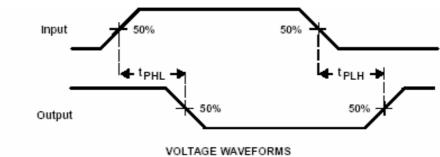
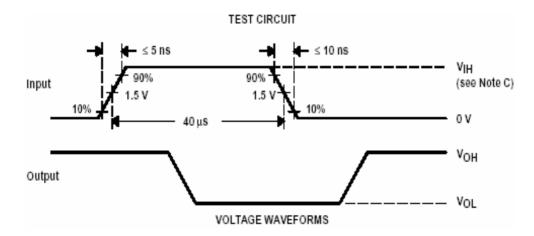


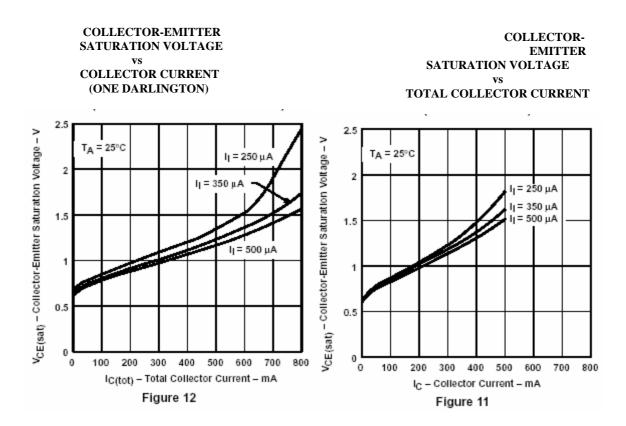
Figure 9. Propagation Delay-Time Waveforms



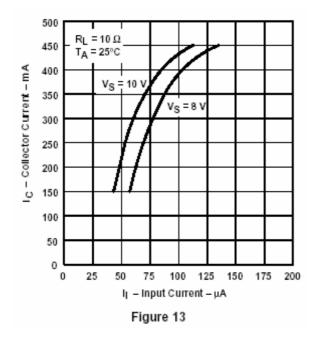
NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_0 = 50$. B. C_L includes probe and jig capacitance. C. $V_{IH} = 3 V;$

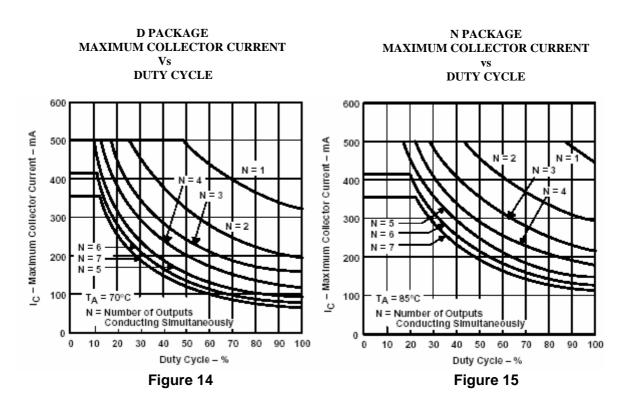
Figure 10. Latch-Up Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS



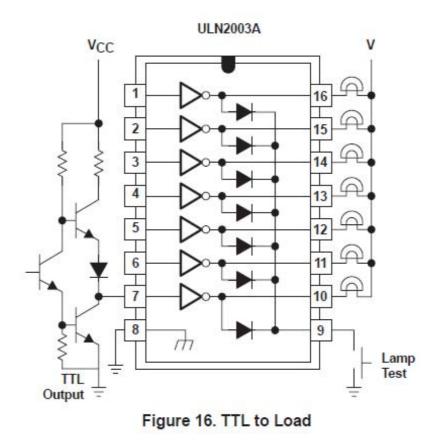
COLLECTOR CURRENT vs INPUT CURRENT



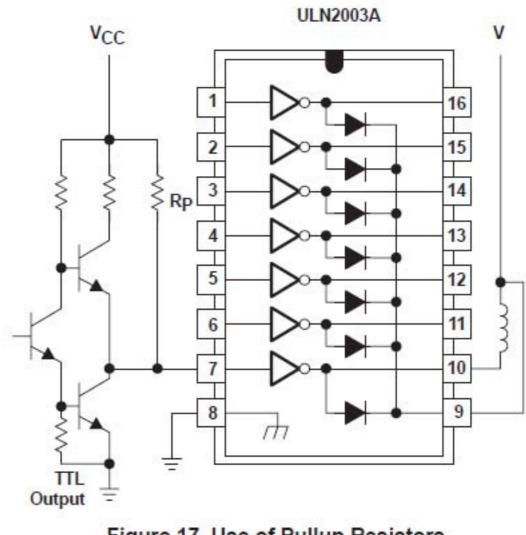


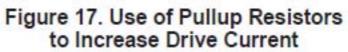
THERMAL INFORMATION

APPLICATION INFORMATION



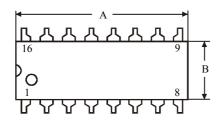
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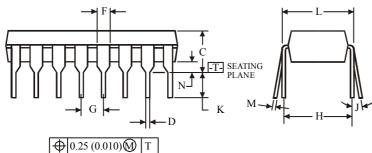




N SUFFIX PLASTIC DIP (MS - 001BB)







NOTES:

 Dimensions "A", "B" do not include mold flash or protrusions. Maximum mold flash or protrusions 0.25 mm (0.010) per side.

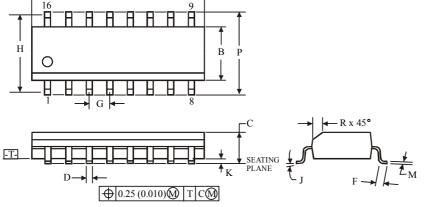
	1			
	Dimension, mm			
Symbol	MIN	MAX		
Α	18.67	19.69		
В	6.10	7.11		
С		5.33		
D	0.36	0.56		
F	1.14	1.78		
G	2.54			
Н	7.62			
J	0°	10°		
K	2.92	3.81		
L	7.62	8.26		
Μ	0.20	0.36		
Ν	0.38			

D SUFFIX SOIC



	Dimension, mm			
Symbol	MIN	MAX		
Α	9.80	10.00		
В	3.80	4.00		
С	1.35	1.75		
D	0.33	0.51		
F	0.40	1.27		
G	1.27 5.72			
Н				
J	0°	8°		
K	0.10	0.25		
М	0.19	0.25		
Р	5.80	6.20		
R	0.25	0.50		

(MS - 012AC)



NOTES:

- 1. Dimensions A and B do not include mold flash or protrusion.
- 2. Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B 0.25 mm (0.010) per side.